



SANYO Semiconductors

DATA SHEET

2SA1575 / 2SC4080 — PNP / NPN Epitaxial Planar Silicon Darlington Transistors

High-Frequency Amplifier, Wide-Band Amplifier Applications

Features

- High f_T .
- High breakdown voltage.
- Small reverse transfer capacitance and excellent high-frequency characteristic.
- Adoption of FBET process.

Specifications () : 2SA1575

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-)200	V
Collector-to-Emitter Voltage	V_{CEO}		(-)200	V
Emitter-to-Base Voltage	V_{EBO}		(-)4	V
Collector Current	I_C		(-)100	mA
Collector Current (Pulse)	I_{CP}		(-)200	mA
Collector Dissipation	P_C		500	mW
		Mounted on a ceramic board (250mm ² X0.8mm)	1.3	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-150\text{V}, I_E=0\text{A}$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-2\text{V}, I_C=0\text{A}$			(-)1.0	μA
DC Current Gain	h_{FE1}	$V_{CE}=-10\text{V}, I_C=-10\text{mA}$	40*		320*	
	h_{FE2}	$V_{CE}=-10\text{V}, I_C=-60\text{mA}$	20			
Gain-Bandwidth Product	f_T	$V_{CE}=-30\text{V}, I_C=-30\text{mA}$		400		MHz
Output Capacitance	C_{ob}	$V_{CB}=-30\text{V}, f=1\text{MHz}$		(2.3)1.8		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=-30\text{V}, f=1\text{MHz}$		(1.7)1.4		pF

Marking : 2SA1575 : AF / 2SC4080 : CI

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* : The 2SA1575 / 2SC4080 are classified by 10mA h_{FE} as follows :

Rank	C	D	E	F
h_{FE}	40 to 80	60 to 120	100 to 200	160 to 320

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2SA1575 / 2SC4080

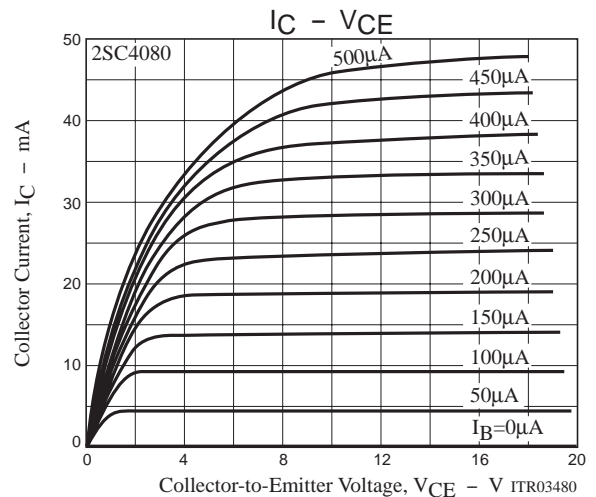
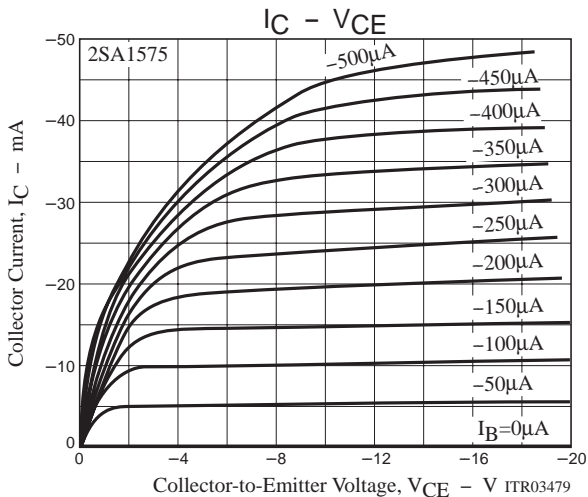
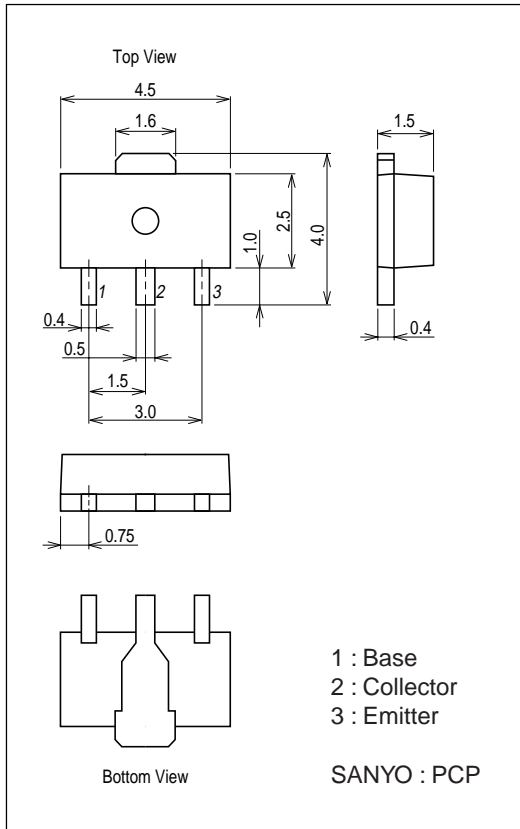
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)20mA, I_B=(-)2mA$			(-) 1.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)20mA, I_B=(-)2mA$			(-) 1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-) 200			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-) 200			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)100\mu A, I_C=0A$	(-) 4			V

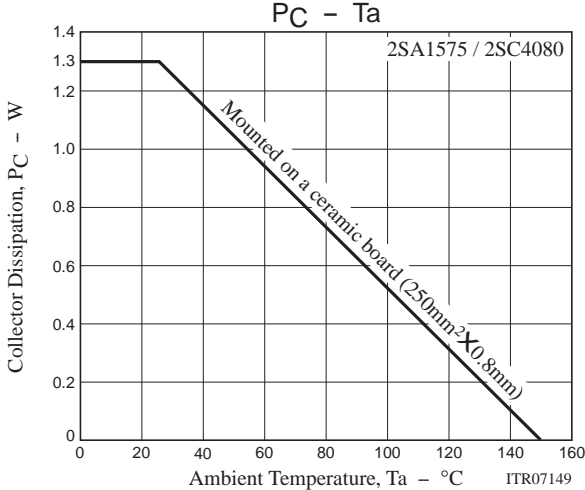
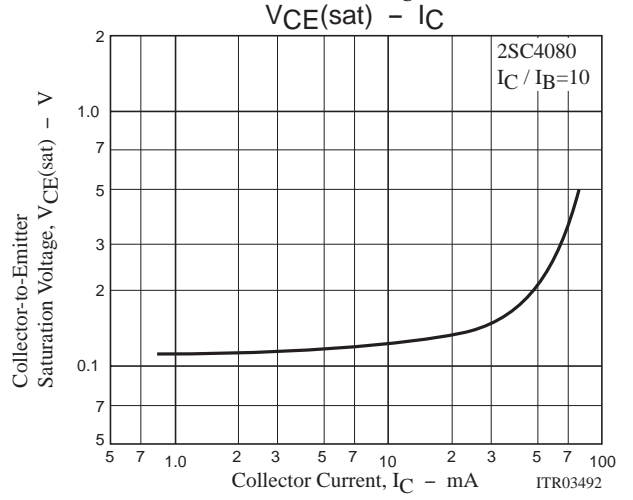
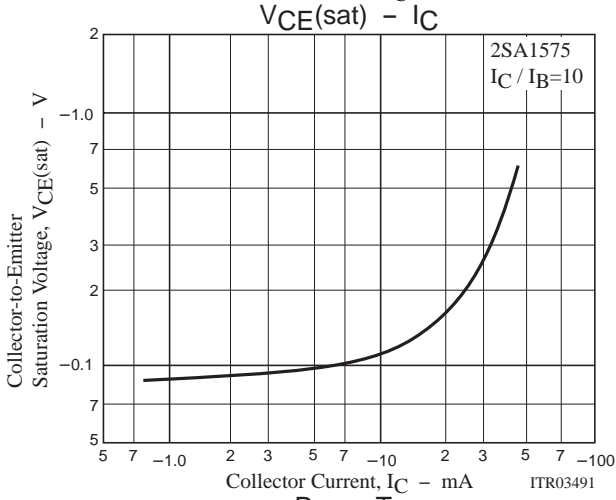
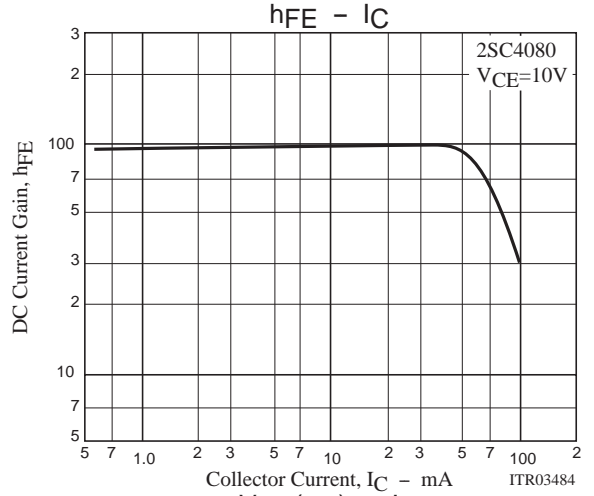
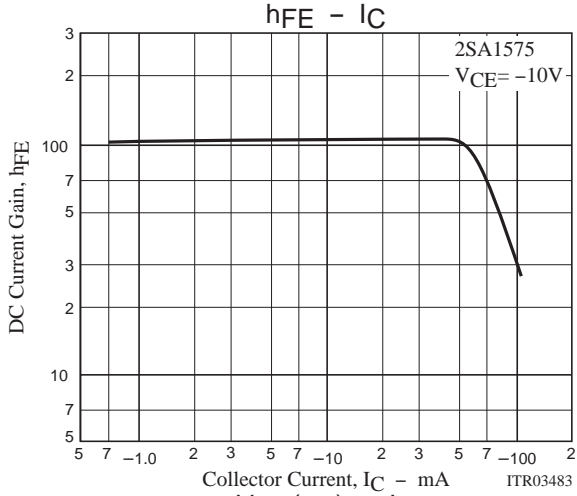
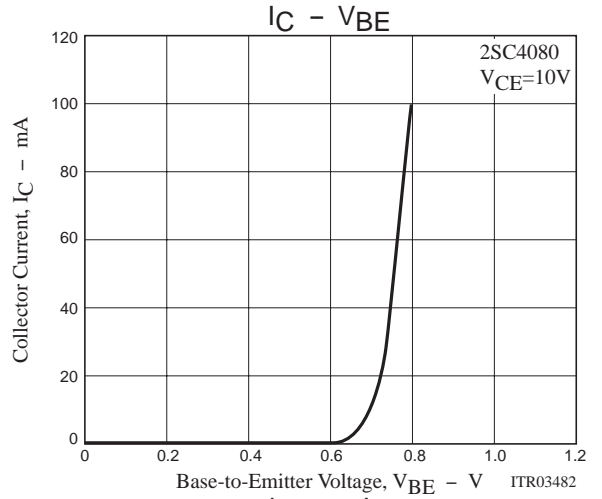
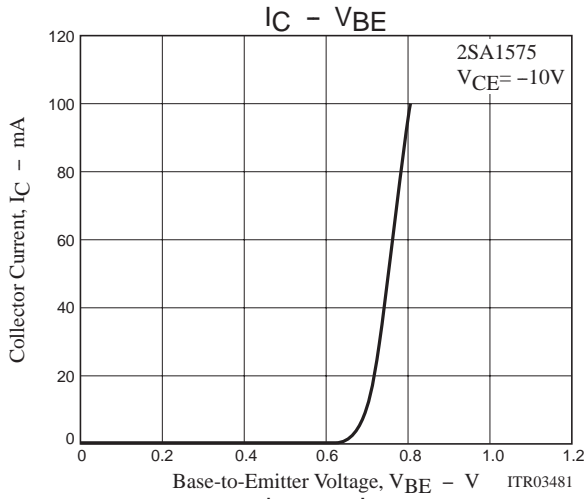
Package Dimensions

unit : mm (typ)

7007A-004



2SA1575 / 2SC4080



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